

# P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)						
- 30	0.035 at V <sub>GS</sub> = - 10 V	- 12 <sup>a</sup>	10 nC						
	0.056 at V <sub>GS</sub> = - 4.5 V	- 12 <sup>a</sup>	10110						

#### **FEATURES**

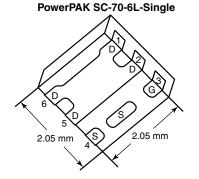
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- Material categorization: For definitions of compliance please see www.vishav.com/doc?99912

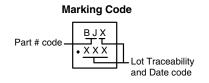


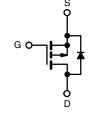
HALOGEN FREE

#### **APPLICATIONS**

- Load Switch for Portable Devices
- **Buck Converter**







Ordering Information: SiA421DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA421DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$\mathbf{S} (1_{A} = 25  {}^{\circ}C,  unlet)$	ess otherwise no	oted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	- 30	V	
Gate-Source Voltage		$V_{GS}$	± 20		
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>		
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 12 <sup>a</sup>	А	
Continuous Diain Curient (1) = 150 C)	T <sub>A</sub> = 25 °C	טי	- 7.9 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		- 6.3 <sup>b, c</sup>		
Pulsed Drain Current	•	I <sub>DM</sub>	- 35		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	- 12 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	'S	- 2.9 <sup>b, c</sup>	1	
	T <sub>C</sub> = 25 °C		19		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	12	W	
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	' D	3.5 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>	1	
Operating Junction and Storage Temperature Ra	ange	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS										
Parameter	Symbol	Typical	Maximum	Unit						
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R <sub>th IC</sub>	5.3	6.5	J 0/W					

#### Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 80 °C/W.

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V			
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 31		mV/°C			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1D = - 250 μΑ		4					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.5		- 3	V			
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA			
Zero Gate Voltage Drain Current	I	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ			
Zero Gate voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10				
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 5 V, $V_{GS}$ = - 10 V	- 20			Α			
	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5.3 A		0.029	0.035	Ω			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 4.2 A		0.046	0.056				
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.3 A		15		S			
Dynamic <sup>b</sup>									
Input Capacitance	C <sub>iss</sub>			950					
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		150		pF			
Reverse Transfer Capacitance	C <sub>rss</sub>			120					
Total Gate Charge	0	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 7.9 A		19	29	nC			
iolai Gale Charge	$Q_g$			10	15				
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -7.9 \text{ A}$		3					
Gate-Drain Charge	$Q_{gd}$			4.5					
Gate Resistance	$R_g$	f = 1 MHz	1.2	6.5	13	Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			40	60				
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 2.4 $\Omega$		110	165				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 6.3 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		25	40				
Fall Time	t <sub>f</sub>			12	20				
Turn-On Delay Time	t <sub>d(on)</sub>			10	15	ns			
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_L = 2.4 \Omega$		12	20				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 6.3 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		30	45				
Fall Time	t <sub>f</sub>			10	15				
Drain-Source Body Diode Characterist	cs								
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	Α			
Pulse Diode Forward Current	I <sub>SM</sub>				35	^			
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 6.3 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t <sub>rr</sub>			20	30	ns			
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>E</sub> = - 6.3 A, dl/dt = 100 A/μs, T <sub>.I</sub> = 25 °C		15	30	nC			
Reverse Recovery Fall Time	t <sub>a</sub>	11F 0.5 A, α//αι = 100 A/μs, 1 <sub>J</sub> = 25 °C		12		20			
Reverse Recovery Rise Time	t <sub>b</sub>			8		ns			

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

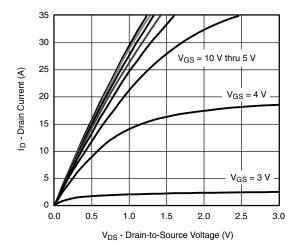
a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

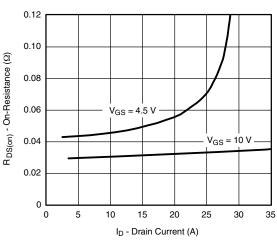




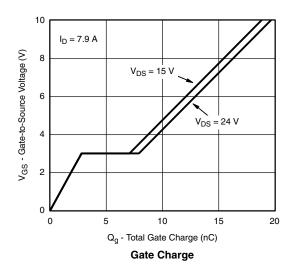
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

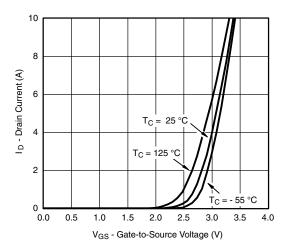


## **Output Characteristics**

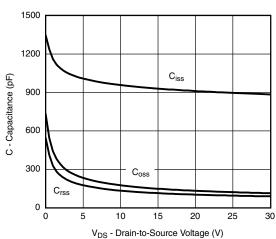


On-Resistance vs. Drain Current and Gate Voltage

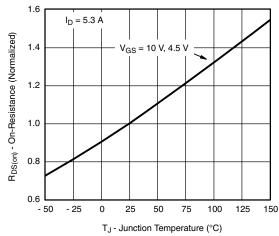




**Transfer Characteristics** 

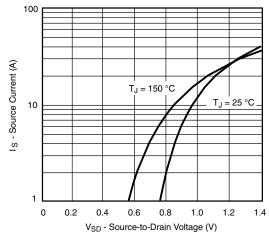


Capacitance

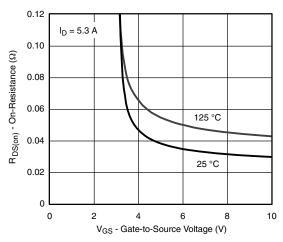


On-Resistance vs. Junction Temperature

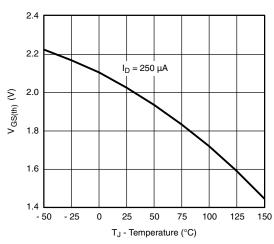
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



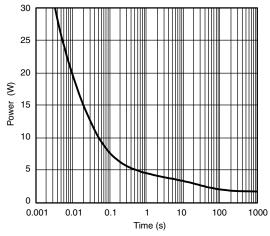
Soure-Drain Diode Forward Voltage



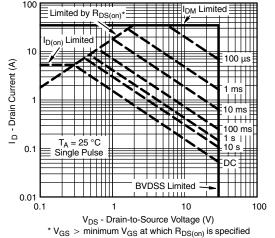
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



Single Pulse Power, Junction-to-Ambient

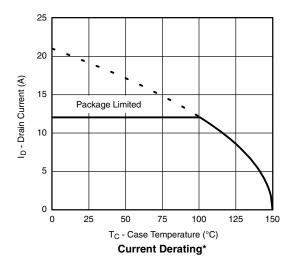


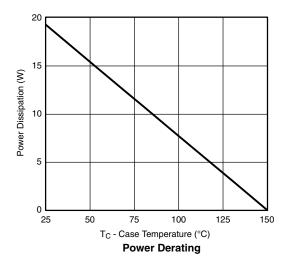
Safe Operating Area, Junction-to-Ambient





## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

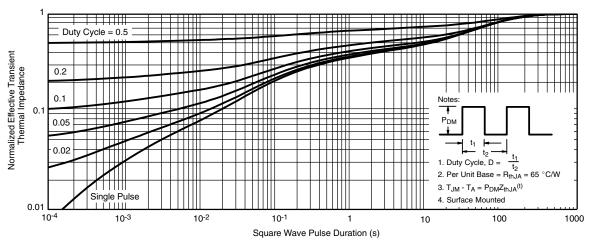




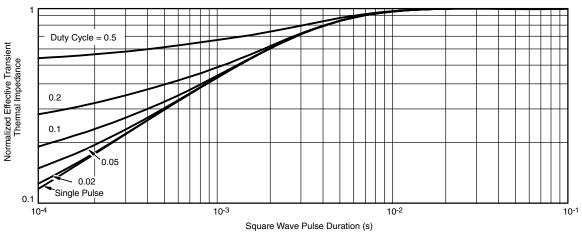
 $<sup>^{\</sup>star}$  The power dissipation  $P_D$  is based on  $T_{J(max.)}$  = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



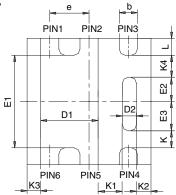
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73975.





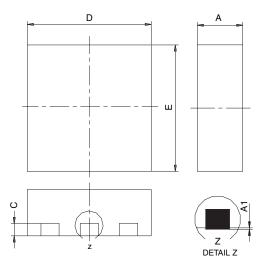
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

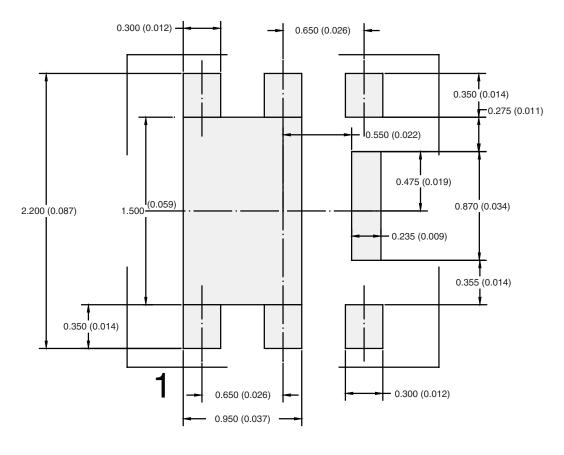
	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP		0.011 TYP			
K1		0.400 TYP	1	0.016 TYP		0.320 TYP		0.013 TYP				
K2		0.240 TYP 0.009 TYP		0.252 TYP			0.010 TYP					
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP	1	0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
FCN: C-07431 - Bey C. 06-Aug-07												

DWG: 5934

Document Number: 73001 06-Aug-07



## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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